

# ISL9R30120G2

## 30 A 1200 V STEALTH™ Diode

### Features

- Stealth Recovery  $t_{rr} = 269$  ns (@  $I_F = 30$  A)
- Max Forward Voltage,  $V_F = 3.3$  V (@  $T_C = 25^\circ\text{C}$ )
- 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

### Applications

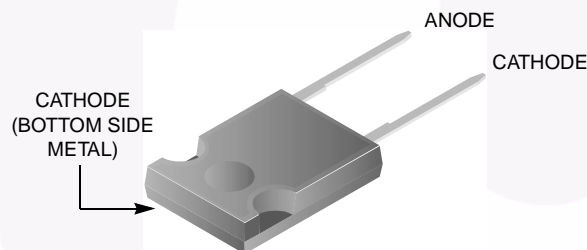
- Switch Mode Power Supplies
- Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- Snubber Diode

### Description

The ISL9R30120G2 is a STEALTH™ diode optimized for low loss performance in high frequency hard switched applications. The STEALTH™ family exhibits low reverse recovery current ( $I_{RR}$ ) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low  $I_{RR}$  and short ta phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

### Package

JEDEC STYLE 2 LEAD TO-247



### Symbol



### Device Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
$V_{RWM}$	Working Peak Reverse Voltage	1200	V
$V_R$	DC Blocking Voltage	1200	V
$I_{F(AV)}$	Average Rectified Forward Current ( $T_C = 80^\circ\text{C}$ )	30	A
$I_{FRM}$	Repetitive Peak Surge Current (20 kHz Square Wave)	70	A
$I_{FSM}$	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60 Hz)	325	A
$P_D$	Power Dissipation	166	W
$E_{AVL}$	Avalanche Energy (1 A, 40 mH)	20	mJ
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	300	$^\circ\text{C}$
$T_{PKG}$	Leads at 0.063 in (1.6 mm) from Case for 10 s Package Body for 10s, See Application Note AN-7528	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

**Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Tape Width	Quantity
ISL9R30120G2	R30120G2	TO-247	Tube	N/A	30

**Electrical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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**Off State Characteristics**

$I_R$	Instantaneous Reverse Current	$V_R = 1200\text{ V}$	$T_C = 25^\circ\text{C}$	-	-	100	$\mu\text{A}$
			$T_C = 125^\circ\text{C}$	-	-	1.0	$\text{mA}$

**On State Characteristics**

$V_F$	Instantaneous Forward Voltage	$I_F = 30\text{ A}$	$T_C = 25^\circ\text{C}$	-	2.8	3.3	$\text{V}$
			$T_C = 125^\circ\text{C}$	-	2.6	3.1	$\text{V}$

**Dynamic Characteristics**

$C_J$	Junction Capacitance	$V_R = 10\text{ V}, I_F = 0\text{ A}$	-	115	-	$\text{pF}$
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**Switching Characteristics**

$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 15\text{ V}$	-	45	56	$\text{ns}$
		$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 15\text{ V}$	-	80	100	$\text{ns}$
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{ A},$ $di_F/dt = 200\text{ A}/\mu\text{s},$ $V_R = 780\text{ V}, T_C = 25^\circ\text{C}$	-	269	-	$\text{ns}$
$I_{rr}$	Reverse Recovery Current		-	7.5	-	$\text{A}$
$Q_{rr}$	Reverse Recovered Charge		-	930	-	$\text{nC}$
$t_{rr}$	Reverse Recovery Time		-	529	-	$\text{ns}$
$S$	Softness Factor ( $t_b/t_a$ )	$I_F = 30\text{ A},$ $di_F/dt = 200\text{ A}/\mu\text{s},$ $V_R = 780\text{ V},$ $T_C = 125^\circ\text{C}$	-	6.2	-	-
$I_{rr}$	Reverse Recovery Current		-	11	-	$\text{A}$
$Q_{rr}$	Reverse Recovered Charge		-	3.0	-	$\mu\text{C}$
$t_{rr}$	Reverse Recovery Time		-	260	-	$\text{ns}$
$S$	Softness Factor ( $t_b/t_a$ )	$I_F = 30\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s},$ $V_R = 780\text{ V},$ $T_C = 125^\circ\text{C}$	-	4.8	-	-
$I_{rr}$	Reverse Recovery Current		-	30	-	$\text{A}$
$Q_{rr}$	Reverse Recovered Charge		-	3.4	-	$\mu\text{C}$
$di_M/dt$	Maximum $di/dt$ during $t_b$		-	520	-	$\text{A}/\mu\text{s}$

**Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance Junction to Case	TO-247	-	-	0.75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	TO-247	-	-	30	$^\circ\text{C}/\text{W}$

## Typical Performance Curves

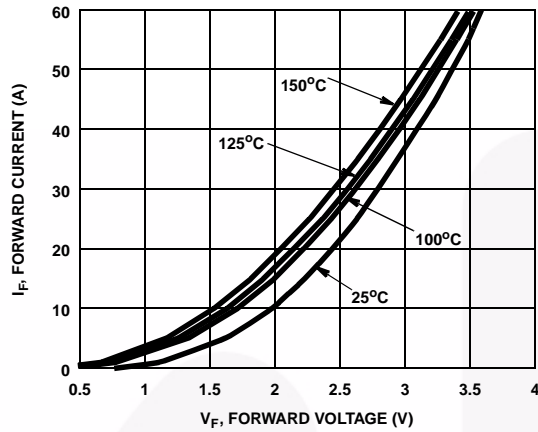


Figure 1. Forward Current vs Forward Voltage

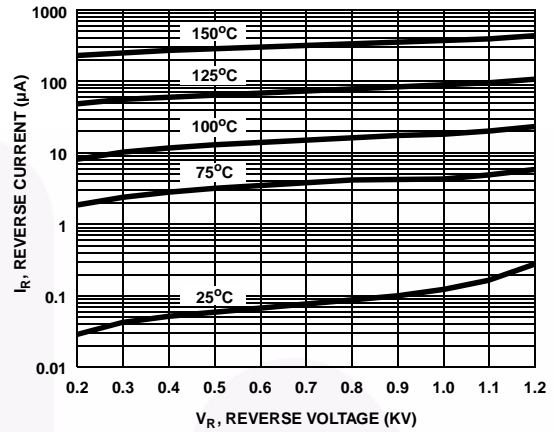


Figure 2. Reverse Current vs Reverse Voltage

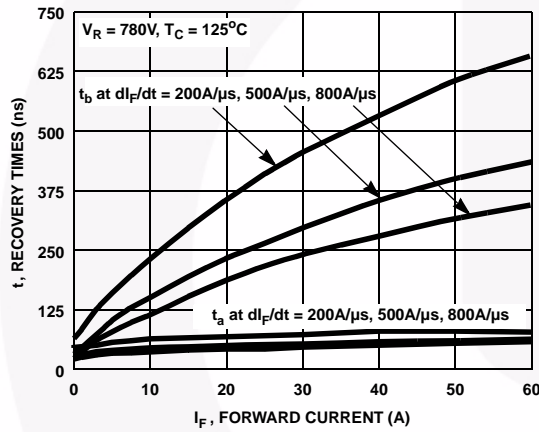


Figure 3.  $t_a$  and  $t_b$  Curves vs Forward Current

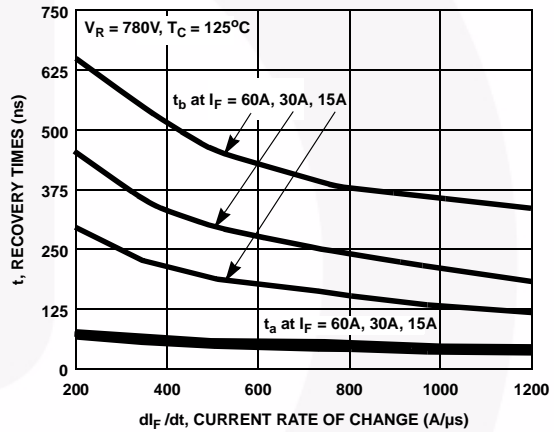


Figure 4.  $t_a$  and  $t_b$  Curves vs  $di_F/dt$

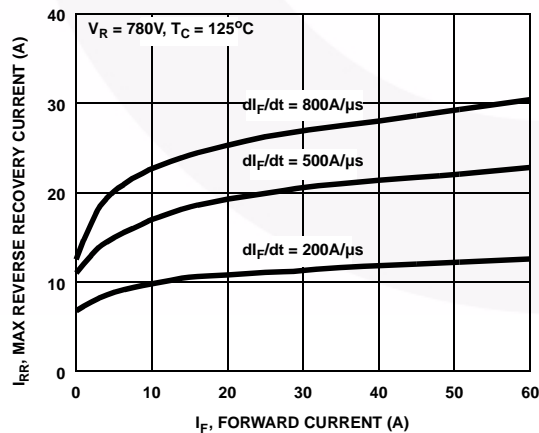


Figure 5. Maximum Reverse Recovery Current vs Forward Current

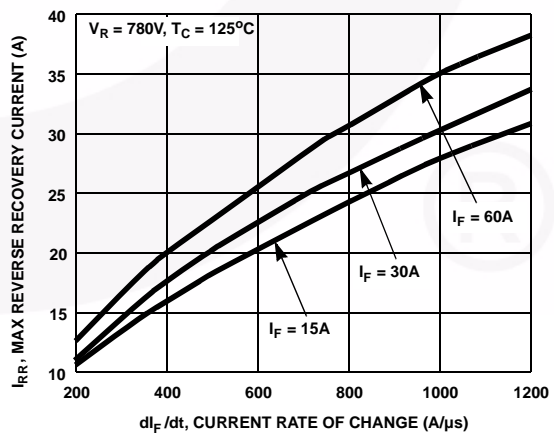


Figure 6. Maximum Reverse Recovery Current vs  $di_F/dt$

Typical Performance Curves (Continued)

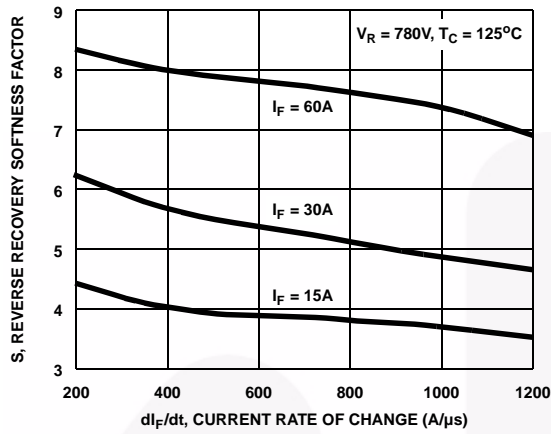


Figure 7. Reverse Recovery Softness Factor vs  $dI_F/dt$

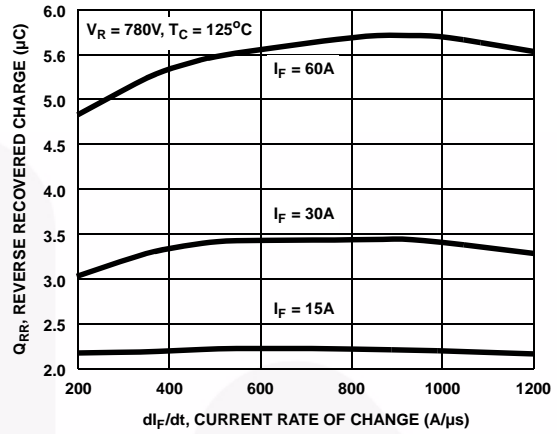


Figure 8. Reverse Recovery Charge vs  $dI_F/dt$

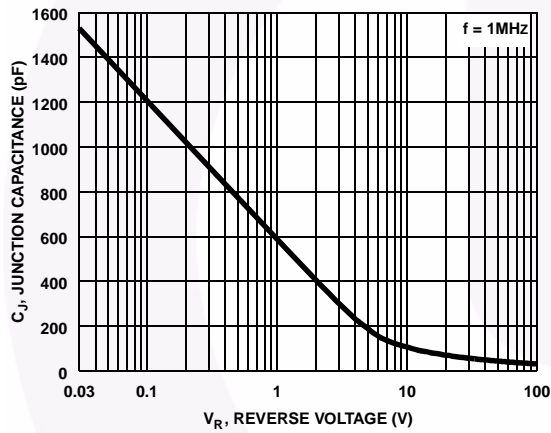


Figure 9. Junction Capacitance vs Reverse Voltage

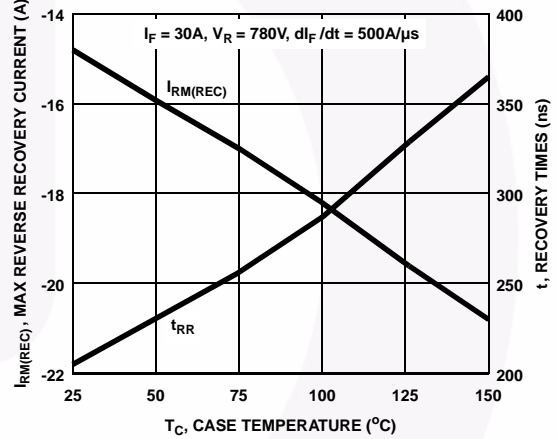


Figure 10. Maximum Reverse Recovery Current and  $t_{rr}$  vs Case Temperature

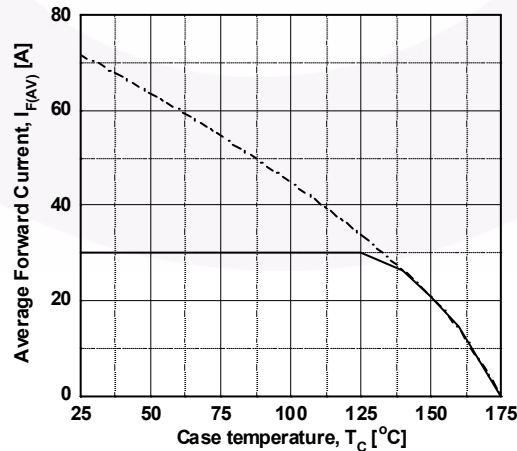
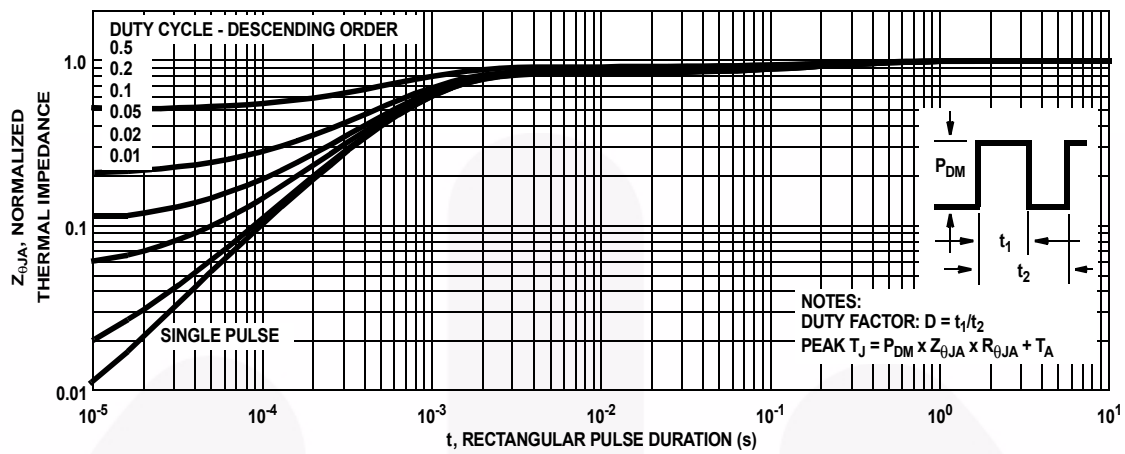


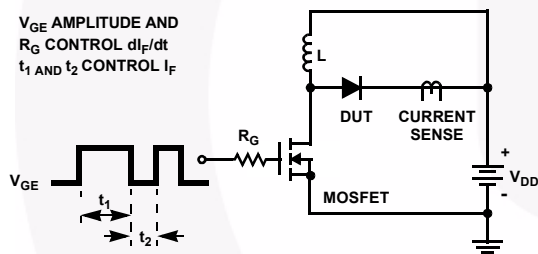
Figure 11. DC Current Derating Curve

### Typical Performance Curves (Continued)

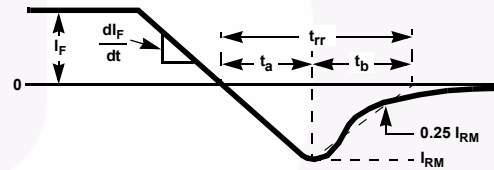


**Figure 12. Normalized Maximum Transient Thermal Impedance**

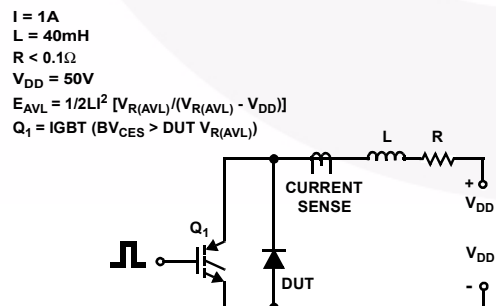
### Test Circuit and Waveforms



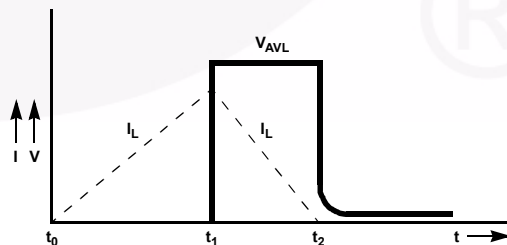
**Figure 13.  $t_{rr}$  Test Circuit**



### Figure 14. $t_{rr}$ Waveforms and Definitions



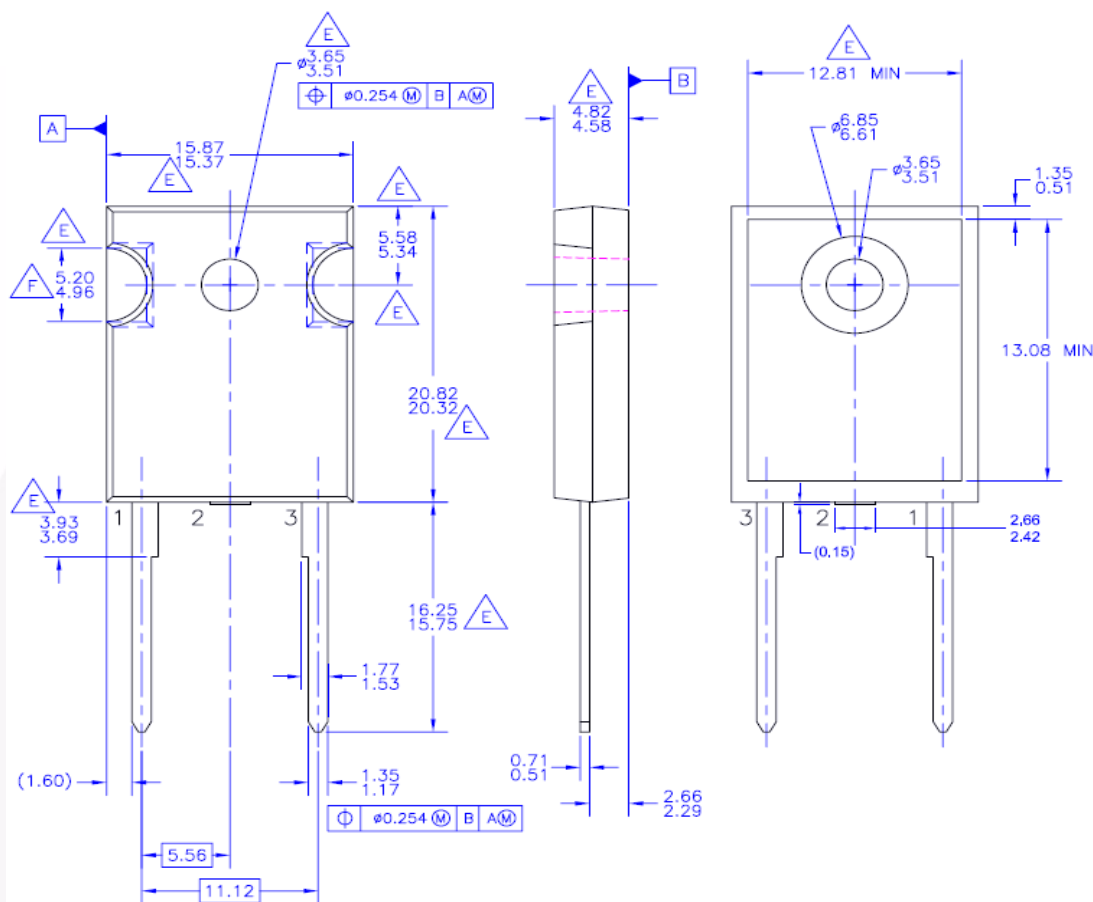
**Figure 15. Avalanche Energy Test Circuit**



### Figure 16. Avalanche Current and Voltage Waveforms

# Mechanical Dimensions

## TO-247 2L



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  - C. ALL DIMENSIONS ARE IN MILLIMETERS.
  - D. DRAWING CONFORMS TO ASME Y14.5 - 1994
  - E. DOES NOT COMPLY JEDEC STANDARD VALUE
  - F. NOTCH MAY BE SQUARE
  - G. DRAWING FILENAME: MKT-TO247B02\_REV02

**Figure 17. TO-247, Molded, 2LD, Jedec Option AB**

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